





#### 100V PNP SILICON LOW SATURATION TRANSISTOR IN SOT23

#### **Features**

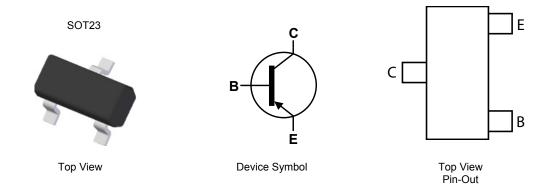
- BV<sub>CEO</sub> > -100V
- I<sub>C</sub> = -1A Continuous Collector Current
- I<sub>CM</sub> = -2.5A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < -330mV @ -1A</li>
- $R_{CE(SAT)} = 210 \text{m}\Omega$  for a low equivalent on-resistance
- 625mW power dissipation
- hFE characterised up to -1.5A for high current gain hold-up
- Complementary NPN Type: FMMT624
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT23
- · Case Material: molded plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight 0.008 grams (approximate)

#### **Applications**

- High-side driver
- Load disconnect switch
- Motor drive



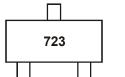
### Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FMMT723TA	723	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com

# **Marking Information**



723 = Product Type Marking Code



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-100	V
Collector-Emitter Voltage	$V_{CEO}$	-100	V
Emitter-Base Voltage	$V_{EBO}$	-7	V
Continuous Collector Current	Ic	-1	Α
Peak Pulse Current	I <sub>CM</sub>	-2.5	Α
Base Current	I <sub>B</sub>	-500	mA

# Thermal Characteristics ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	625	mW
Power Dissipation (Note 6)	P <sub>D</sub>	806	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	200	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	155	°C/W
Thermal Resistance, Junction to Leads (Note 7)	R <sub>θJL</sub>	194	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

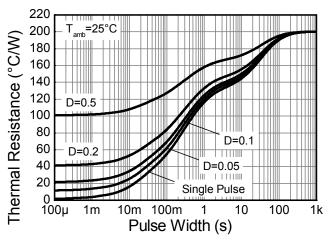
Notes:

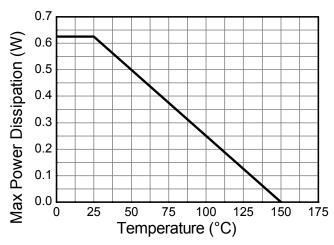
- 5. For a device surface mounted on 25mm X 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 6. Same as note 5, except the device is measured at  $t \le 5$  sec.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



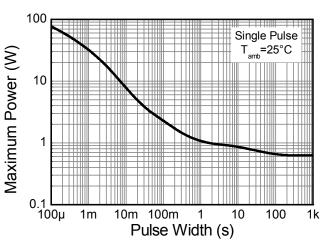


# **Thermal Characteristics and Derating information**

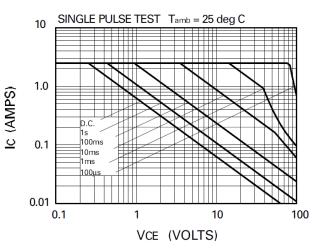




# **Transient Thermal Impedance**



**Derating Curve** 



**Pulse Power Dissipation** 

Safe Operating Area



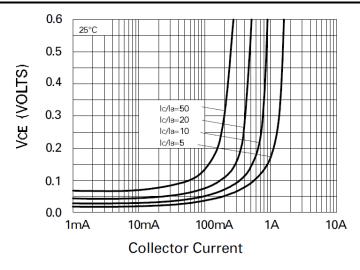
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

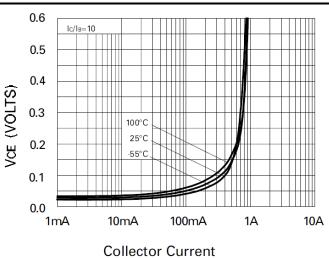
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-100	-200	-	V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-100	-160	-	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	-8.8	-	V	I <sub>E</sub> = -100μA
Collector Cutoff Current	I <sub>CBO</sub>	-	<1	-100	nA	V <sub>CB</sub> = -80V
Emitter Cutoff Current	I <sub>EBO</sub>	-	<1	-100	nA	$V_{EB} = -5.6V$
Collector Emitter Cutoff Current	I <sub>CES</sub>	-	<1	-100	nA	V <sub>CE</sub> = -80V
		300	475	-		$I_C = -10 \text{mA}, V_{CE} = -10 \text{V}$
		300	450	-		$I_C = -0.1A$ , $V_{CE} = -10V$
Static Forward Current Transfer Ratio (Note 9)	$h_{FE}$	250	375	-	-	$I_C = -0.5A$ , $V_{CE} = -10V$
		-	250	-		$I_C = -1A$ , $V_{CE} = -10V$
		-	30	-		I <sub>C</sub> = -1.5A, V <sub>CE</sub> = -10V
		-	-50	-80		$I_C = -0.1A$ , $I_B = -10mA$
Collector-Emitter Saturation Voltage (Note 9)	$V_{CE(sat)}$	-	-125	-200	mV	$I_C = -0.5A$ , $I_B = -50mA$
		-	-210	-330		$I_C = -1A$ , $I_B = -150mA$
Base-Emitter Turn-On Voltage(Note 9)	$V_{BE(on)}$	-	-0.71	-1.0	V	$I_C = -1A$ , $V_{CE} = -10V$
Base-Emitter Saturation Voltage(Note 9)	$V_{BE(sat)}$	-	-0.89	-1.0	V	$I_C = -1A$ , $I_B = -150mA$
Output Capacitance	$C_{obo}$	-	13	20	pF	V <sub>CB</sub> = -10V, f = 1MHz
Transition Frequency	f <sub>T</sub>	150	200	-	MHz	$V_{CE} = -10V, I_{C} = -50mA,$ f = 100MHz
Turn-On Time	t <sub>on</sub>	-	50	-	ns	$V_{CC} = -50V, I_{C} = -0.5A$
Turn-Off Time	t <sub>off</sub>	-	760	-	ns	$I_{B1} = I_{B2} = -50 \text{mA}$

Notes: 9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%

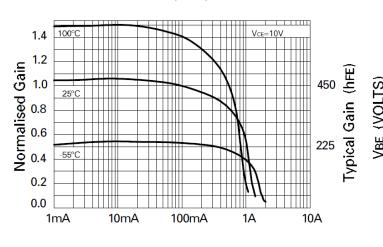


# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

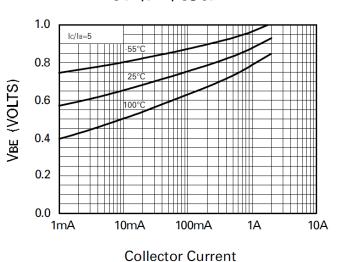




## VCE(SAT) vs IC

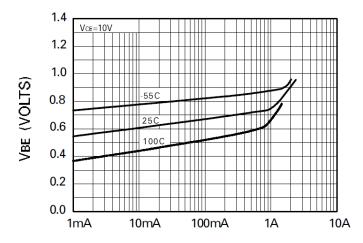


VCE(SAT) vs IC



### **Collector Current**

hfe vs IC



Collector Current

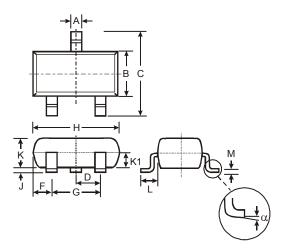
### VBE(ON) vs IC

VBE(SAT) vs IC



# **Package Outline Dimensions**

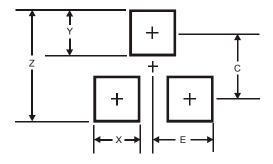
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.903	1.10	1.00		
K1	-	-	0.400		
L	0.45	0.61	0.55		
M	0.085	0.18	0.11		
α	0°	8°	-		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
Е	1.35





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